

5DS21M

Switching Diode



Features

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- High-speed (Common Cathode)

Item	Characteristics
Wafer size	5inch
Chip size	390*390um
Pad size	150*150*212um
Scribe line width	50um
Top Metalization	Al
Chip Quantity	71,552pcs/wafer

Maximum Ratings @25degC

Item	Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage	VRSM	80	V
Repetitive Peak Reverse Voltage	VRRM	80	V
Repetitive Peak Forward Current	IFRM	300	mA
Continuous Forward Current	IO	100	mA
Non-Repetitive Peak Forward Current @t=1us	IFSM	4.0	A
Power Dissipation	PD	200	mW
Junction Temperature	Tj	150	degC
Storage Temperature	Tstg	-55to+150	degC

Electrical Characteristics @25degC

Item	Symbol	Min	Max	Unit	Test Condition
Forward Voltage	VF		1.2	V	IF=100mA
Breakdown Voltage	BV	80		V	IR=100uA
Reverse Current	IR		100.0	nA	VR=70V
Capacitance	CT		2.0	pF	VR=0V, f=1MHz
Reverse Recovery Time	trr		4.0	nsec	IF=5mA, VR=6V, RL=100Ω, irr=1mA

Wafer Probing Spec @25degC

Symbol	Min	Max	Unit	Test Condition
VF		1.15	V	IF=100mA
BV	90		V	IR=100uA
IR1		25	nA	VR=30V
IR2		90	nA	VR=70V

Ordering Information

Chip Type	Chip Thickness	Back Metalization
5DS21MS	180±15um	Au/As (For Eutectic)
5DS21MQ	135±15um	Au/As-Au (For AgEpoxy/Eutectic)

Note

Equivalent type :

SheetNo.

Rev.